Transistors with Built-in Resistor

DRA3114T0L

DRA3114T0L

Panasonic

Silicon PNP epitaxial planar type

For digital circuits
Complementary to DRC3114T
DRA9114T in SSSMini3 type package

■ Features

- · High forward current transfer ratio hFE with excellent linearity
- · Low collector-emitter saturation voltage Vce(sat)
- Halogen-free / RoHS compliant (EU RoHS / UL-94 V-0 / MSL:Level 1 compliant)
- Marking Symbol: LD

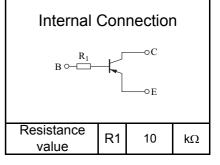
■ Packaging

Embossed type (Thermo-compression sealing): 10 000 pcs / reel (standard)

■ Absolute Maximum Ratings Ta = 25 °C

Parameter	Symbol	Rating	Unit
Collector-base voltage (Emitter open)	VCBO	-50	V
Collector-emitter voltage (Base open)	VCEO	-50	V
Collector current	IC	-100	mA
Total power dissipation	PT	100	mW
Junction temperature	Tj	150	°C
Operating ambient temperature	Topr	-40 to +85	°C
Storage temperature	Tstg	-55 to +150	°C

Unit: mm 1.2 0.3 0. 13 0. 2 0.52 (0.4) (0.4) 0.8 1. Base 2. Emitter 3. Collector Panasonic SSSMini3-F2-B JEITA SC-105AA Code SOT-723



■ Electrical Characteristics Ta = 25 °C ± 3 °C

Established: 2009-10-23

: 2014-02-07

Revised

Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Collector-base voltage (Emitter open)	VCBO	$IC = -10 \mu A, IE = 0$	-50			V
Collector-emitter voltage (Base open)	VCEO	IC = -2 mA, IB = 0	-50			V
Collector-base cutoff current (Emitter open)	ICBO	VCB = -50 V, IE = 0			-0.1	μΑ
Collector-emitter cutoff current (Base open)	ICEO	VCE = -50 V, IB = 0			-0.5	μΑ
Emitter-base cutoff current (Collector open)	IEBO	VEB = -6 V, IC = 0			-0.01	mA
Forward current transfer ratio	hFE	VCE = -10 V, IC = -5 mA	160		460	-
Collector-emitter saturation voltage	VCE(sat)	IC = -10 mA, IB = -0.5 mA			-0.25	V
Input voltage	Vi(on)	VCE = -0.2 V, IC = -5 mA	-1.2			V
	Vi(off)	VCE = -5 V, IC = -100 μA			-0.4	V
Input resistance	R1		-30%	10	+30%	kΩ

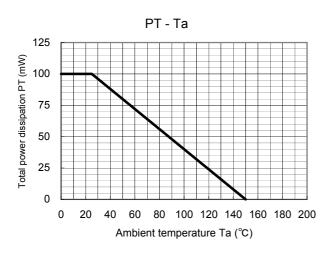
 $Note) \, 1. \quad \text{Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 Measuring methods for transistors.}$

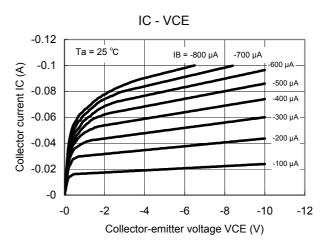
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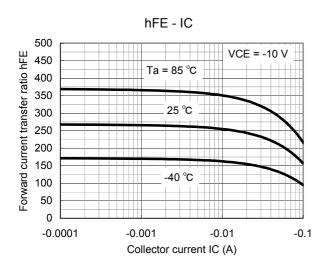
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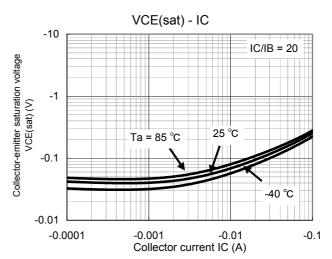
Panasonic

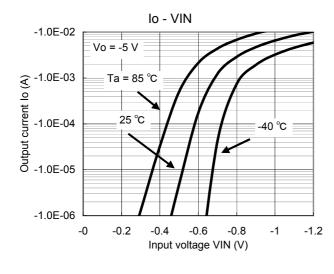
Technical Data (reference)

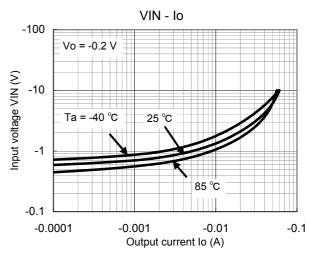












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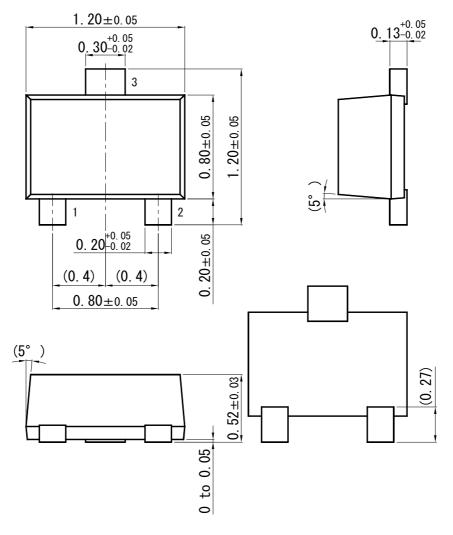
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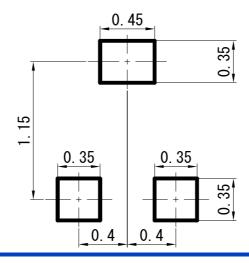
SSSMini3-F2-B

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Unit: mm



■ Land Pattern (Reference) (Unit: mm)



Page 3 of 3

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